TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

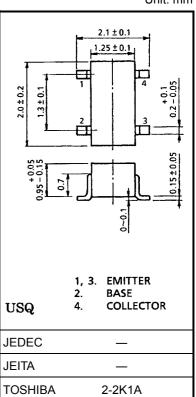
2SC5088

VHF~UHF Band Low Noise Amplifier Applications

- Low noise figure, high gain.
- NF = 1.1dB, $|S_{21e}|^2 = 13dB$ (f = 1 GHz)

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Collector-base voltage	V _{CBO}	20	V	
Collector-emitter voltage	V _{CEO}	12	V	
Emitter-base voltage	V _{EBO}	3	V	
Base current	Ι _Β	40	mA	
Collector current	۱ _C	80	mA	
Collector power dissipation	P _C	100	mW	
Junction temperature	Tj	125	°C	
Storage temperature range	T _{stg}	-55~125	°C	



Weight: 0.006 g (typ.)

Microwave Characteristics (Ta = 25°C)

				1			
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Transition frequency	fT	$V_{CE} = 10 \text{ V}, \text{ I}_{C} = 20 \text{ mA}$	5	7	_	GHz	
Insertion gain	S _{21e} ² (1)	V_{CE} = 10 V, I_C = 20 mA, f = 500 MHz	—	18		- dB	
	S _{21e} ² (2)	$V_{CE}=10~V,~I_{C}=20~mA,~f=1~GHz$	9.5	13			
Noise figure	NF (1)	$V_{CE}=10~V,~I_C=5~mA,~f=500~MHz$	_	1	_	dB	
	NF (2)	$V_{CE} = 10 \text{ V}, \text{ I}_{C} = 5 \text{ mA}, \text{ f} = 1 \text{ GHz}$	_	1.1	2	uВ	

Electrical Characteristics (Ta = 25°C)

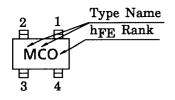
Characteristics Symbol		Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = 10 \text{ V}, \text{ I}_{E} = 0$	_	_	1	μA
Emitter cut-off current	I _{EBO}	$V_{EB} = 1 V, I_{C} = 0$	_	_	1	μA
DC current gain	h _{FE} (Note 1)	$V_{CE} = 10 \text{ V}, \text{ I}_{C} = 20 \text{ mA}$	80	_	240	
Output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz (Note 2)	_	1.1	1.6	pF
Reverse transfer capacitance	C _{re}	VCB = 10 V, 1E = 0, 1 = 1 MHZ (NOLE 2)	_	0.65	1.05	pF

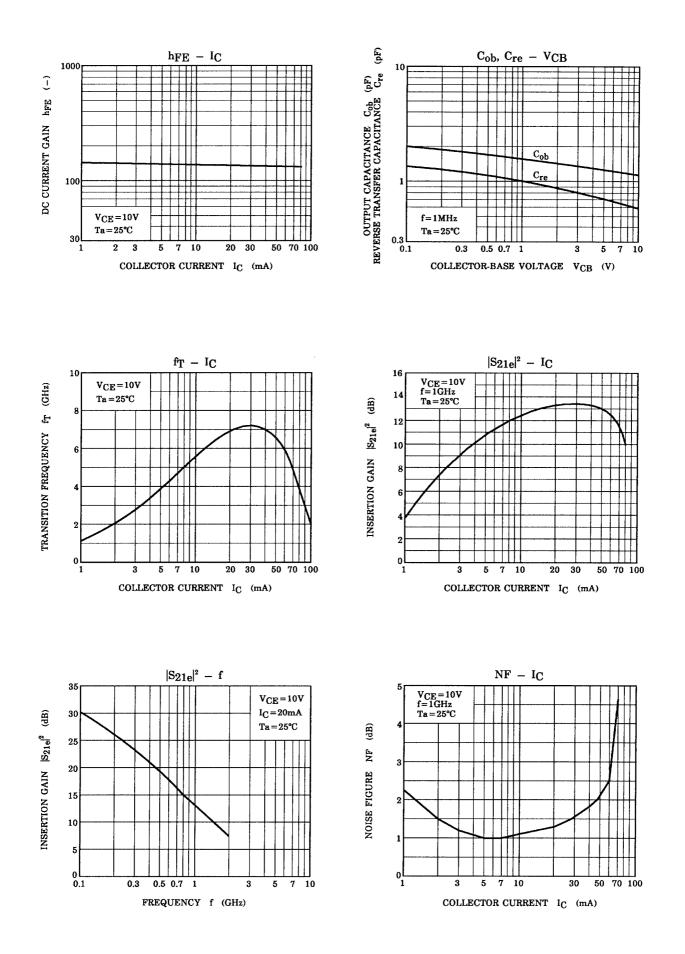
Note 1: hFE classification O: 80~160, Y: 120~240

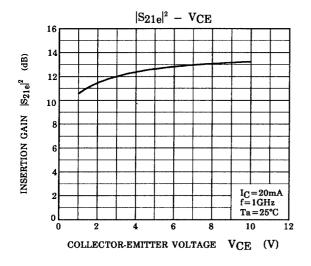
Note 2: C_{re} is measured by 3 terminal method with capacitance bridge.

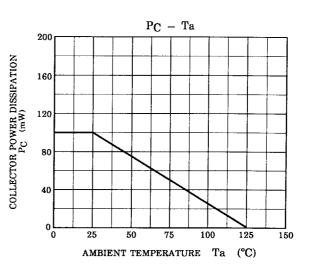
Unit: mm

Marking









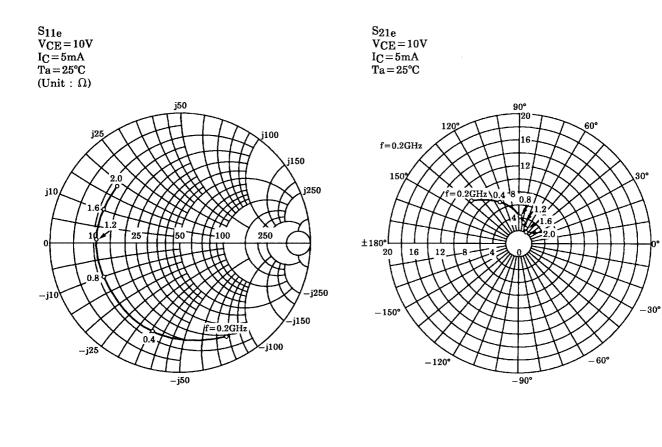
S-Parameter $Z_0 = 50 \Omega$, Ta = 25°C

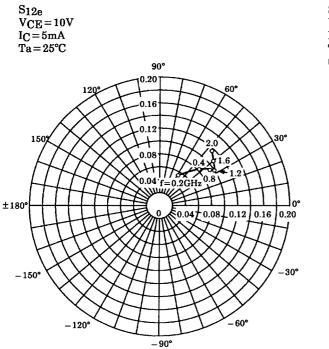
$V_{CE} = 10 \text{ V}, I_C = 5 \text{ mA}$

Frequency	S11		S21		S12		S22	
(MHz)	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.
200	0.826	-64.3	9.839	139.2	0.056	59.2	0.844	-31.7
400	0.735	-106.8	7.058	115.2	0.083	43.8	0.663	-50.1
600	0.692	-134.4	5.233	99.5	0.094	36.8	0.558	-62.3
800	0.666	-154.3	4.106	88.1	0.100	33.3	0.496	-72.6
1000	0.656	-170.0	3.315	78.9	0.102	32.7	0.458	-81.8
1200	0.653	178.0	2.768	71.3	0.103	33.4	0.429	-90.6
1400	0.649	167.7	2.353	65.4	0.104	36.0	0.407	-99.4
1600	0.655	158.2	2.061	59.6	0.107	39.1	0.393	-107.8
1800	0.653	149.0	1.818	55.3	0.111	42.6	0.378	-115.3
2000	0.654	139.9	1.650	50.7	0.116	46.7	0.367	-121.9

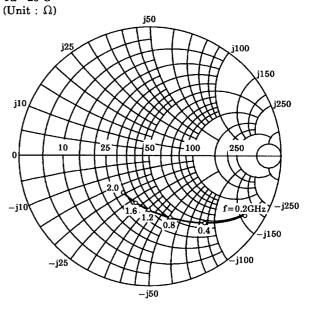
$V_{CE} = 10 \text{ V}, I_C = 20 \text{ mA}$

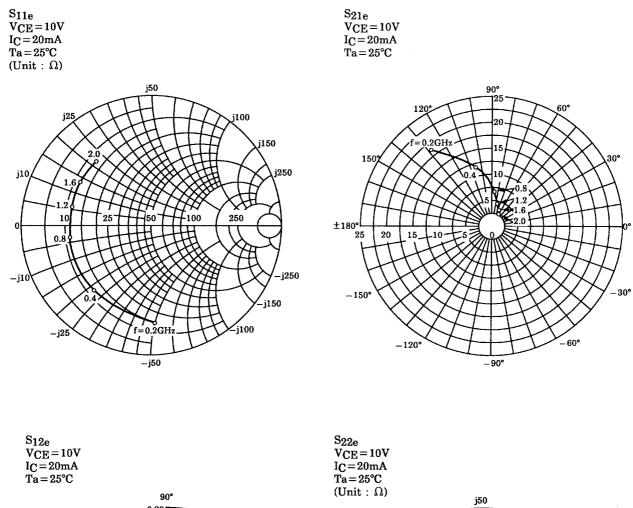
Frequency	S11		S21		S12		S22	
(MHz)	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.
200	0.747	-87.0	16.492	129.8	0.048	52.1	0.717	-47.1
400	0.675	-130.5	10.431	106.5	0.063	41.8	0.486	-69.1
600	0.648	-154.8	7.298	93.5	0.070	40.8	0.379	-82.0
800	0.636	-170.9	5.547	84.4	0.076	42.0	0.324	-93.0
1000	0.630	176.7	4.423	77.5	0.083	44.7	0.291	-102.7
1200	0.634	166.4	3.660	71.7	0.089	47.7	0.266	-112.1
1400	0.634	157.1	3.125	67.0	0.097	50.8	0.249	-120.8
1600	0.639	148.8	2.741	62.4	0.105	53.2	0.233	-128.9
1800	0.645	139.9	2.451	58.8	0.115	55.6	0.220	-135.8
2000	0.642	131.4	2.233	54.9	0.126	58.1	0.205	-141.2

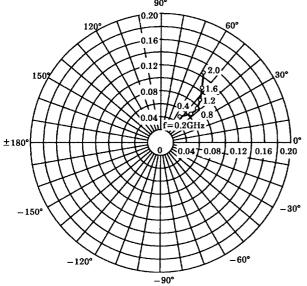


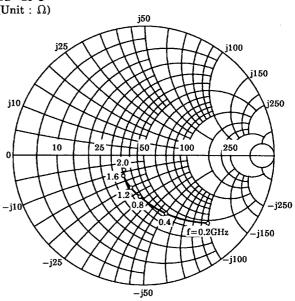


 S_{22e} $V_{CE} = 10V$ $I_{C} = 5mA$ $T_{a} = 25^{\circ}C$









RESTRICTIONS ON PRODUCT USE

- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
 In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.

This datasheet has been download from:

www.datasheetcatalog.com

Datasheets for electronics components.